

Features

- Epitaxial Planar Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ideally Suited for Automated Assembly Processes
- **Lead Free By Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)

Mechanical Data

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: Collector Dot (See Diagram)
- Terminals: Finish — NiPdAu annealed over Copper leadframe.
Solderable per MIL-STD-202, Method 208
- Marking Code N5, Dot denotes Collector Side
- Ordering Information: See Page 4
- Weight: 0.001 grams (approximate)

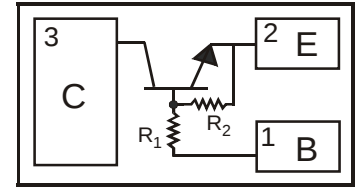
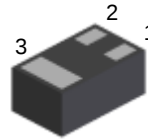
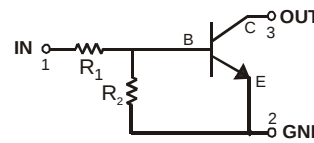
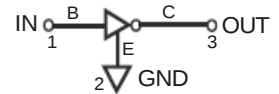


Fig. 1



Schematic and Pin Configuration



Equivalent Inverter Circuit

Fig. 2

Component P/N	R1(NOM)	R2(NOM)	Figure
DDTC114ELP	10K	10K	2

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current	I _O	50	mA
Power Dissipation (Note 3)	P _d	250	mW
Power Deration above 25°C	P _{der}	2	mW/°C
Collector Current	I _{C(max)}	100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Junction Operation and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air (Note 3) (Equivalent to one heated junction of NPN)	R _{θJA}	400	°C/W

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, 1" x 0.85" x 0.062"; pad layout as shown on page 5 or Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

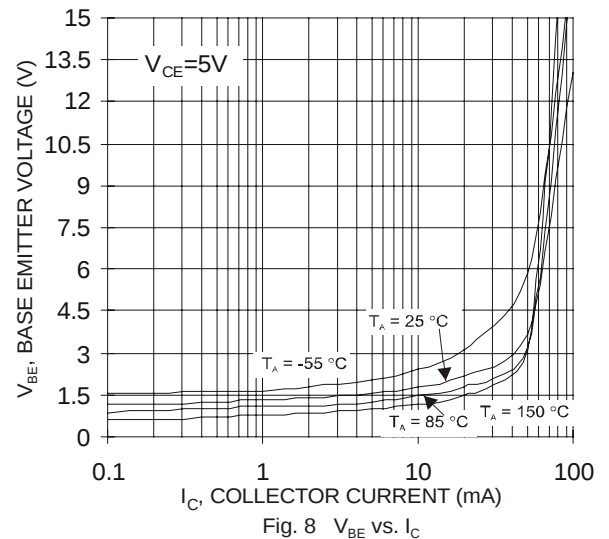
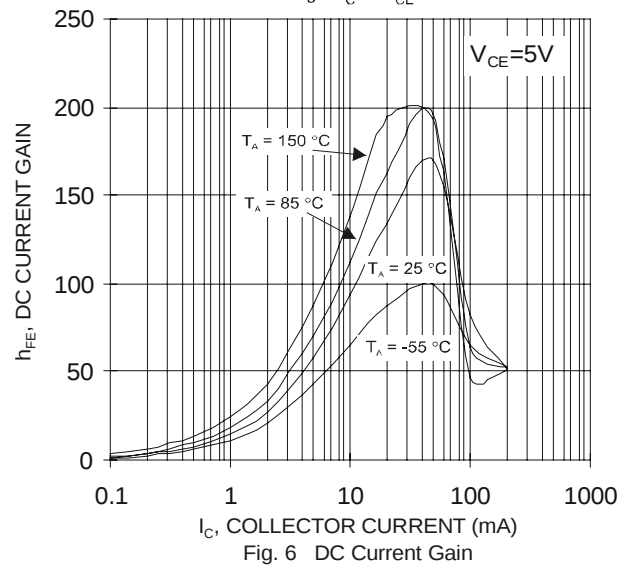
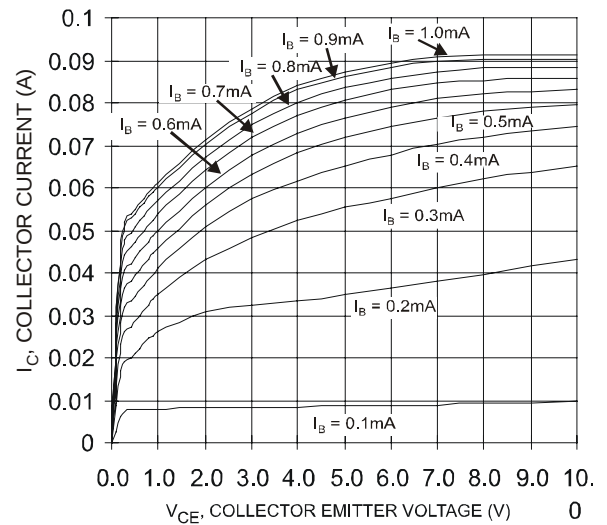
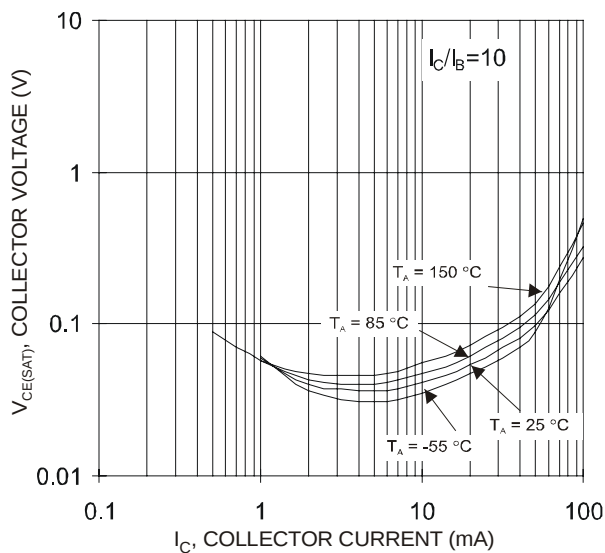
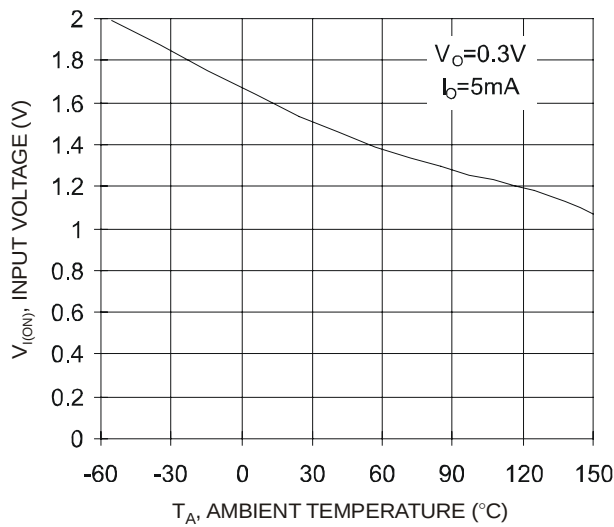
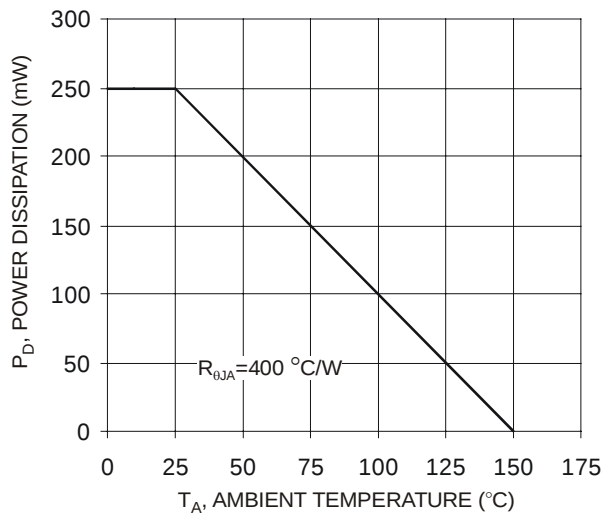
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Off Characteristics (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50	—	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	50	—	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage*	V _{(BR)EBO}	5	—	—	V	I _E = 50μA, I _C = 0
Collector Cutoff Current*	I _{CEX}	—	—	0.5	μA	V _{CE} = 50V, V _{EB(OFF)} = 3.0V
Base Cutoff Current (I _{BEX})	I _{BL}	—	—	0.5	μA	V _{CE} = 50V, V _{EB(OFF)} = 3.0V
Collector-Base Cut Off Current	I _{CBO}	—	—	0.5	μA	V _{CB} = 50V, I _E = 0
Collector-Emitter Cut Off Current, I _{O(OFF)}	I _{CEO}	—	—	1	μA	V _{CB} = 50V, I _B = 0
Emitter-Base Cut Off Current	I _{EBO}	—	—	0.4	mA	V _{EB} = 4V, I _C = 0
Input Off Voltage	V _{I(OFF)}	—	1.16	0.5	V	V _{CC} = 5V, I _O = 100uA
On Characteristics (Note 4)						
DC Current Gain	h _{FE}	10	—	—	—	V _{CE} = 5V, I _C = 1mA
		15	—	—	—	V _{CE} = 5V, I _C = 2mA
		60	—	—	—	V _{CE} = 5V, I _C = 10mA
		100	—	—	—	V _{CE} = 5V, I _C = 50mA
		90	—	—	—	V _{CE} = 5V, I _C = 70mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	0.15	V	I _C = 10mA, I _B = 1mA
		—	—	0.2	V	I _C = 50mA, I _B = 5mA
		—	—	0.25	V	I _C = 50mA, I _B = 2.5mA
		—	—	0.25	V	I _C = 50mA, I _B = 10mA
		—	—	0.3	V	I _C = 70mA, I _B = 10mA
Base-Emitter Turn-On Voltage*	V _{BE(ON)}	—	—	0.85	V	V _{CE} = 5V, I _C = 2mA
		—	—	0.95	V	V _{CE} = 5V, I _C = 10mA
Base-Emitter Saturation Voltage*	V _{BE(SAT)}	—	—	0.98	V	I _C = 10mA, I _B = 1mA, V _{CE} = 5V
		—	—	1.2	V	I _C = 50mA, I _B = 5mA, V _{CE} = 5V
Input-On Voltage	V _{I(ON)}	2.5	1.6	—	V	V _O = 0.3V, I _O = 50mA
Input Current	I _I	—	—	0.88	mA	V _I = 5V
Output On Voltage (Same as V _{CE(SAT)})	V _{O(ON)}	—	—	0.3	V	I _I = 2.5mA, I _O = 50mA
Input Resistance	R _I	7	10	13	KΩ	—
Resistance Ratio	(R ₂ /R ₁)	0.8	1	1.2	—	—
Small Signal Characteristics						
Current Gain-Bandwidth Product	f _T	—	250	—	MHz	V _{CE} = 10V, I _E = 5mA, f = 1MHz

* Guaranteed by design.

Note: 4. Short duration test pulse used to minimize self-heating effect.
Pulse Test: Pulse width tp<300 us, Duty Cycle, d<=2%.

Typical Characteristics Curves

@T_A = 25°C unless otherwise specified



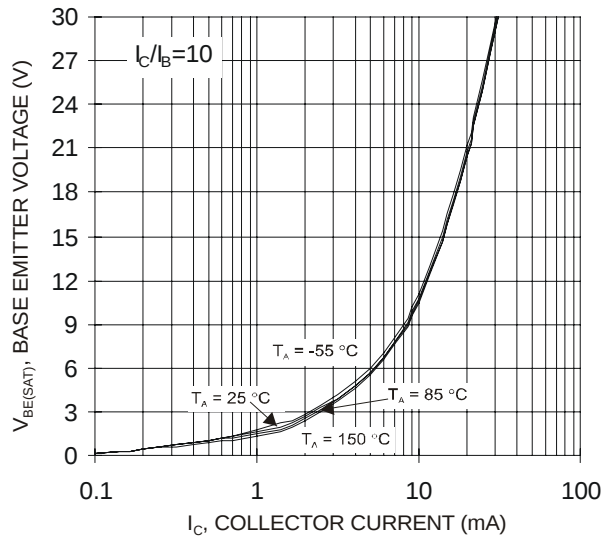


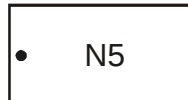
Fig. 9 $V_{BE(SAT)}$ vs. I_C

Ordering Information (Note 6)

Device	Marking Code	Packaging	Shipping
DDTC114ELP-7	N5	DFN1006-3	3000/Tape & Reel

Notes: 6. For packaging details, please see page 5 or go to our website at <http://www.diodes.com/ap2007.pdf>.

Marking Information



N5 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month e.g. 9 = September

Fig. 13

Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions

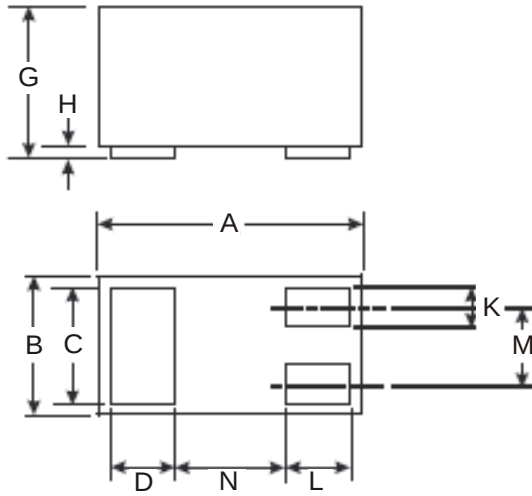


Fig. 14

DFN1006-3			
Dim	Min	Max	Typ
A	0.95	1.05	1.00
B	0.55	0.65	0.60
C	0.45	0.55	0.50
D	0.20	0.30	0.25
G	0.47	0.53	0.50
H	0	0.05	0.03
K	0.10	0.20	0.15
L	0.20	0.30	0.25
M	—	—	0.35
N	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout: (Based on IPC-SM-782)

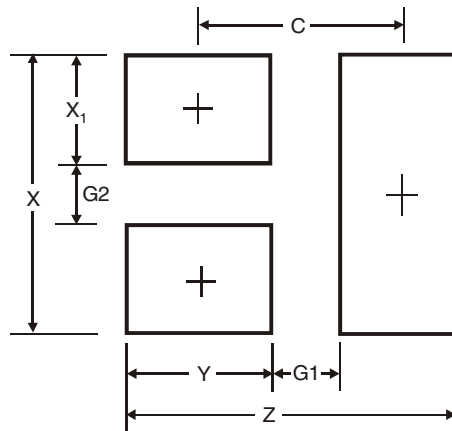


Fig. 15

DFN1006-3	
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7
All Dimensions in mm	

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